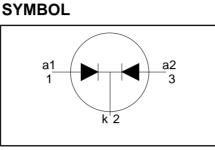
PBYR30100WT series

QUICK REFERENCE DATA

 $V_{R} = 60 \text{ V}/80 \text{ V}/100 \text{ V}$

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance



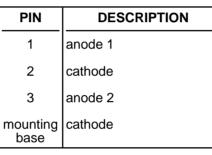
PINNING

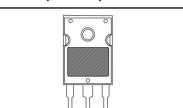
$I_{O(AV)} = 30 \text{ A}$ $V_F \le 0.7 \text{ V}$

GENERAL DESCRIPTION

Schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR30100WT series is supplied in the conventional leaded SOT429 (TO247) package.





2

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
		PBYR30		60WT	80WT	100WT	
V _{RRM}	Peak repetitive reverse		-	60	80	100	V
V _{RWM}	voltage Working peak reverse voltage		-	60	80	100	V
V _R	Continuous reverse voltage	T _{mb} ≤ 139 °C	-	60	80	100	V
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; δ = 0.5; $T_{mb} \le$ 124 °C	-		30		А
I _{FRM}	Repetitive peak forward current per diode	square wave; δ = 0.5; T _{mb} \leq 124 °C	-	30		A	
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125$ °C prior to surge; with reapplied V _{RPM(max)}	-		180 200		A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{j max}	-		1		A
T _j	Operating junction temperature	Jimax	-	150		°C	
T _{stg}	Storage temperature		- 65		175		°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb} R _{th j-a}	to mounting base	per diode both diodes in free air		- - 45	1.4 1 -	K/W K/W K/W

PBYR30100WT series

ELECTRICAL CHARACTERISTICS

characteristics are per diode at T_j = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	I _F = 15 A; T _i = 125°C I _F = 30 A; T _i = 125°C	-	0.61	0.7	V
	5	I _F = 30 A; T _i = 125°C	-	0.74	0.85	V
		$I_{\rm F} = 15 {\rm A}$	-	0.77	0.85	V
I _R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	5	150	μA
i î		$V_{R}^{K} = V_{RWM}^{KWM}; T_{j} = 125^{\circ}C_{T}$	-	5	15	mΑ
C _d	Junction capacitance	$V_{R}^{R} = 5 \text{ V}; \text{ f} = 1 \text{ MHz}, \text{ T}_{j} = 25 \text{ °C to } 125 \text{ °C}$	-	600	-	pF

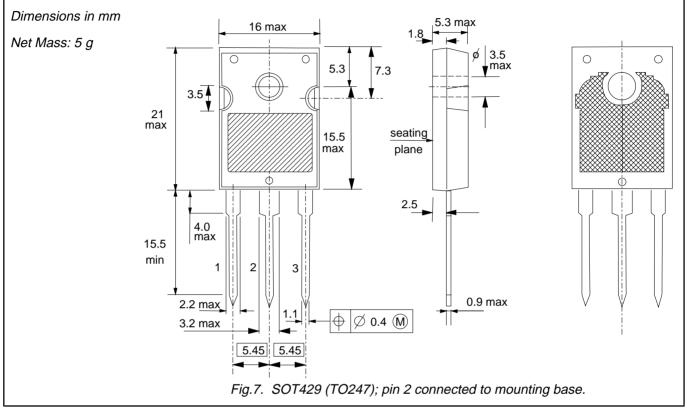
PBYR30100WT series

Rectifier diodes Schottky barrier

IR/ mA Tmb(max) / C 122 PF/W 100 20 Vo = 0.5 Rs = 0.010 $\dot{D} = 1.0$ Ti/ C = 150 10 15 129 0.5 125 0: 100 10 136 1 h 1 . 75 to р 5 143 0.1 _50 150 0 0.01 10 26 20 50 60 VR/ V 70 10 20 30 40 80 90 100 IF(AV) / A Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per Fig.4. Typical reverse leakage current per diode; diode; square current waveform where $I_R = f(V_R)$; parameter T_i $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$ Cd/ pF Tmb(max) / C PF/W 10000 129 15 Vo = 0.550 s = 0.010 O a = 1.57 q 10 136 1000 4 5 143 100 150 0 10 5 15 10 0 10 VR/ V 100 IF(AV) / A Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form Fig.5. Typical junction capacitance per diode; $C_d = f(V_R); f = 1 \text{ MHz}; T_j = 25^{\circ}C \text{ to } 125^{\circ}C.$ factor = $I_{F(RMS)} / I_{F(AV)}$. Transient thermal impedance, Zth j-mb (K/W) IF / A 10 100 Tj = 25 C = 125 C Τi 80 1 60 0.1 40 0.01 tρ D 20 0.001 └─ 1us T ----0 1ms 10ms 100ms 1s 10us 100us 10s Ó 0.5 1.5 2 pulse width, tp (s) VF / V Fig.3. Typical and maximum forward characteristic Fig.6. Transient thermal impedance per diode; per diode; $I_F = f(V_F)$; parameter T_i $Z_{th j-mb} = f(t_p).$

PBYR30100WT series

MECHANICAL DATA



Notes

Refer to mounting instructions for SOT429 envelope.
Epoxy meets UL94 V0 at 1/8".

PBYR30100WT series

DEFINITIONS

Data sheet status				
Objective specification	jective specification This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	ecification This data sheet contains final product specifications.			
Limiting values				
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application information is given, it is advisory and does not form part of the specification.				
© Philips Electronics N.V. 1998				
All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.				
The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.				

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.